

# MOSFET – SiC Power, Single N-Channel, TO247-3L

## 900 V, 20 mΩ, 118 A

### NVHL020N090SC1

#### Features

- Typ.  $R_{DS(on)} = 20 \text{ m}\Omega$
- Ultra Low Gate Charge (typ.  $Q_{G(tot)} = 196 \text{ nC}$ )
- Low Effective Output Capacitance (typ.  $C_{oss} = 296 \text{ pF}$ )
- 100% UIL Tested
- Qualified According to AEC-Q101
- RoHS Compliant

#### Typical Applications

- Automotive On Board Charger
- Automotive DC/DC Converter for EV/HEV

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter                                                                                               |                                                                       |                        | Symbol                            | Value       | Unit |
|---------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------|------------------------|-----------------------------------|-------------|------|
| Drain-to-Source Voltage                                                                                 |                                                                       |                        | V <sub>DSS</sub>                  | 900         | V    |
| Gate-to-Source Voltage                                                                                  |                                                                       |                        | V <sub>GS</sub>                   | +19/-10     | V    |
| Recommended Operation Values of Gate – Source Voltage                                                   |                                                                       | T <sub>C</sub> < 175°C | V <sub>GSop</sub>                 | +15/-5      | V    |
| Continuous Drain Current R <sub>θJC</sub>                                                               | Steady State                                                          | T <sub>C</sub> = 25°C  | I <sub>DC</sub>                   | 118         | A    |
| Power Dissipation R <sub>θJC</sub>                                                                      |                                                                       |                        | P <sub>DC</sub>                   | 503         | W    |
| Continuous Drain Current R <sub>θJC</sub>                                                               | Steady State                                                          | T <sub>C</sub> = 100°C | I <sub>DC</sub>                   | 83          | A    |
| Power Dissipation R <sub>θJC</sub>                                                                      |                                                                       |                        | P <sub>DC</sub>                   | 251         | W    |
| Pulsed Drain Current (Note 2)                                                                           |                                                                       | T <sub>A</sub> = 25°C  | I <sub>DM</sub>                   | 472         | A    |
| Single Pulse Surge Drain Current Capability (Note 3)                                                    | T <sub>A</sub> = 25°C, t <sub>p</sub> = 10 μs, R <sub>G</sub> = 4.7 Ω |                        | I <sub>DSC</sub>                  | 854         | A    |
| Operating Junction and Storage Temperature Range                                                        |                                                                       |                        | T <sub>J</sub> , T <sub>stg</sub> | -55 to +175 | °C   |
| Source Current (Body Diode)                                                                             |                                                                       |                        | I <sub>S</sub>                    | 153         | A    |
| Single Pulse Drain-to-Source Avalanche Energy (I <sub>L</sub> = 23 A <sub>pk</sub> , L = 1 mH) (Note 4) |                                                                       |                        | E <sub>AS</sub>                   | 264         | mJ   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

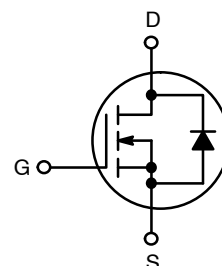
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. Peak current might be limited by transconductance.
4.  $E_{AS}$  of 264 mJ is based on starting  $T_J = 25^\circ\text{C}$ ;  $L = 1 \text{ mH}$ ,  $I_{AS} = 23 \text{ A}$ ,  $V_{DD} = 100 \text{ V}$ ,  $V_{GS} = 15 \text{ V}$ .



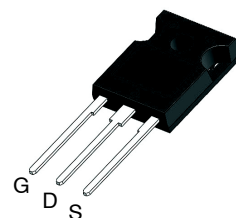
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| $V_{(BR)DSS}$ | $R_{DS(on)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 900 V         | 28 mΩ @ 15 V             | 118 A             |

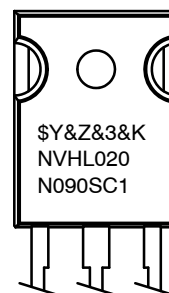


N-CHANNEL MOSFET



TO-247 LONG LEADS  
CASE 340CX

#### MARKING DIAGRAM



$\$Y$  = ON Semiconductor Logo  
 $\&Z$  = Assembly Plant Code  
 $\&3$  = Date Code (Year & Week)  
 $\&K$  = Lot  
 NVHL020N090SC1 = Specific Device Code

#### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

**Table 1. THERMAL CHARACTERISTICS**

| Parameter                                       | Symbol          | Max  | Units                |
|-------------------------------------------------|-----------------|------|----------------------|
| Thermal Resistance Junction-to-Case (Note 1)    | $R_{\theta JC}$ | 0.30 | $^{\circ}\text{C/W}$ |
| Thermal Resistance Junction-to-Ambient (Note 1) | $R_{\theta JA}$ | 40   | $^{\circ}\text{C/W}$ |

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}\text{C}$  unless otherwise stated)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

**OFF CHARACTERISTICS**

|                                                           |                   |                                                     |                             |     |         |                              |
|-----------------------------------------------------------|-------------------|-----------------------------------------------------|-----------------------------|-----|---------|------------------------------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$     | $V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$            | 900                         |     |         | V                            |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | $I_D = 1\text{ mA}$ , refer to $25^{\circ}\text{C}$ |                             | 500 |         | $\text{mV}/^{\circ}\text{C}$ |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$         | $V_{GS} = 0\text{ V}$<br>$V_{DS} = 900\text{ V}$    | $T_J = 25^{\circ}\text{C}$  |     | 100     | $\mu\text{A}$                |
|                                                           |                   |                                                     | $T_J = 175^{\circ}\text{C}$ |     | 250     | $\mu\text{A}$                |
| Gate-to-Source Leakage Current                            | $I_{GSS}$         | $V_{GS} = +19/-10\text{ V}, V_{DS} = 0\text{ V}$    |                             |     | $\pm 1$ | $\mu\text{A}$                |

**ON CHARACTERISTICS**

|                               |              |                                                                      |     |     |     |                  |
|-------------------------------|--------------|----------------------------------------------------------------------|-----|-----|-----|------------------|
| Gate Threshold Voltage        | $V_{GS(TH)}$ | $V_{GS} = V_{DS}, I_D = 20\text{ mA}$                                | 1.8 | 2.7 | 4.3 | V                |
| Recommended Gate Voltage      | $V_{GOP}$    |                                                                      | -5  |     | +15 | V                |
| Drain-to-Source On Resistance | $R_{DS(on)}$ | $V_{GS} = 15\text{ V}, I_D = 60\text{ A}, T_J = 25^{\circ}\text{C}$  |     | 20  | 28  | $\text{m}\Omega$ |
|                               |              | $V_{GS} = 15\text{ V}, I_D = 60\text{ A}, T_J = 175^{\circ}\text{C}$ |     | 27  |     | $\text{m}\Omega$ |
| Forward Transconductance      | $g_{FS}$     | $V_{DS} = 20\text{ V}, I_D = 60\text{ A}$                            |     | 49  |     | S                |

**CHARGES, CAPACITANCES & GATE RESISTANCE**

|                              |              |                                                                          |  |      |  |          |
|------------------------------|--------------|--------------------------------------------------------------------------|--|------|--|----------|
| Input Capacitance            | $C_{ISS}$    | $V_{GS} = 0\text{ V}, f = 1\text{ MHz},$<br>$V_{DS} = 450\text{ V}$      |  | 4415 |  | pF       |
| Output Capacitance           | $C_{OSS}$    |                                                                          |  | 296  |  |          |
| Reverse Transfer Capacitance | $C_{RSS}$    |                                                                          |  | 24   |  |          |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = -5/15\text{ V}, V_{DS} = 720\text{ V},$<br>$I_D = 60\text{ A}$ |  | 196  |  | nC       |
| Threshold Gate Charge        | $Q_{G(TH)}$  |                                                                          |  | 42   |  |          |
| Gate-to-Source Charge        | $Q_{GS}$     |                                                                          |  | 78   |  |          |
| Gate-to-Drain Charge         | $Q_{GD}$     |                                                                          |  | 55   |  |          |
| Gate-Resistance              | $R_G$        | $f = 1\text{ MHz}$                                                       |  | 1.6  |  | $\Omega$ |

**SWITCHING CHARACTERISTICS**

|                         |              |                                                                                                                      |  |      |  |               |
|-------------------------|--------------|----------------------------------------------------------------------------------------------------------------------|--|------|--|---------------|
| Turn-On Delay Time      | $t_{d(ON)}$  | $V_{GS} = -5/15\text{ V}, V_{DS} = 720\text{ V},$<br>$I_D = 60\text{ A}, R_G = 2.5\text{ }\Omega,$<br>Inductive Load |  | 40   |  | ns            |
| Rise Time               | $t_r$        |                                                                                                                      |  | 63   |  |               |
| Turn-Off Delay Time     | $t_{d(OFF)}$ |                                                                                                                      |  | 55   |  |               |
| Fall Time               | $t_f$        |                                                                                                                      |  | 13   |  |               |
| Turn-On Switching Loss  | $E_{ON}$     |                                                                                                                      |  | 2025 |  | $\mu\text{J}$ |
| Turn-Off Switching Loss | $E_{OFF}$    |                                                                                                                      |  | 201  |  |               |
| Total Switching Loss    | $E_{TOT}$    |                                                                                                                      |  | 2226 |  |               |

**DRAIN-SOURCE DIODE CHARACTERISTICS**

|                                                    |           |                                                                        |  |     |     |   |
|----------------------------------------------------|-----------|------------------------------------------------------------------------|--|-----|-----|---|
| Continuous Drain-Source Diode Forward Current      | $I_{SD}$  | $V_{GS} = -5\text{ V}, T_J = 25^{\circ}\text{C}$                       |  |     | 153 | A |
| Pulsed Drain-Source Diode Forward Current (Note 2) | $I_{SDM}$ | $V_{GS} = -5\text{ V}, T_J = 25^{\circ}\text{C}$                       |  |     | 472 | A |
| Forward Diode Voltage                              | $V_{SD}$  | $V_{GS} = -5\text{ V}, I_{SD} = 30\text{ A}, T_J = 25^{\circ}\text{C}$ |  | 3.8 |     | V |

**Table 2. ELECTRICAL CHARACTERISTICS** ( $T_J = 25^\circ\text{C}$  unless otherwise stated)

| Parameter                                 | Symbol    | Test Condition                                                                                                       | Min | Typ | Max | Unit          |
|-------------------------------------------|-----------|----------------------------------------------------------------------------------------------------------------------|-----|-----|-----|---------------|
| <b>DRAIN-SOURCE DIODE CHARACTERISTICS</b> |           |                                                                                                                      |     |     |     |               |
| Reverse Recovery Time                     | $t_{RR}$  | $V_{GS} = -5/15\text{ V}$ , $I_{SD} = 60\text{ A}$ , $dI_S/dt = 1000\text{ A}/\mu\text{s}$ , $V_{DS} = 720\text{ V}$ |     | 28  |     | ns            |
| Reverse Recovery Charge                   | $Q_{RR}$  |                                                                                                                      |     | 199 |     | nC            |
| Reverse Recovery Energy                   | $E_{REC}$ |                                                                                                                      |     | 4   |     | $\mu\text{J}$ |
| Peak Reverse Recovery Current             | $I_{RRM}$ |                                                                                                                      |     | 14  |     | A             |
| Charge time                               | $T_a$     |                                                                                                                      |     | 16  |     | ns            |
| Discharge time                            | $T_b$     |                                                                                                                      |     | 12  |     | ns            |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

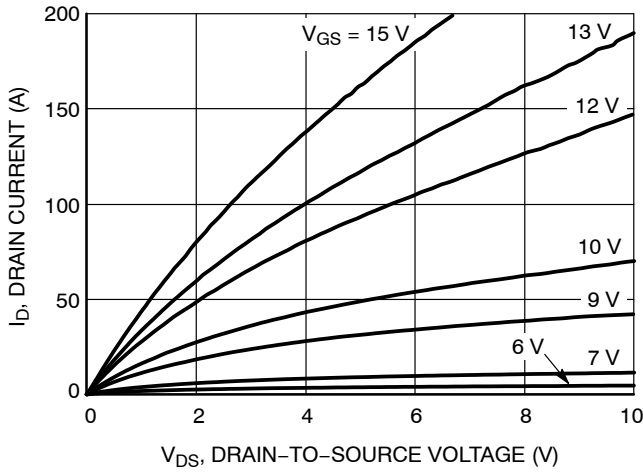


Figure 1. On-Region Characteristics

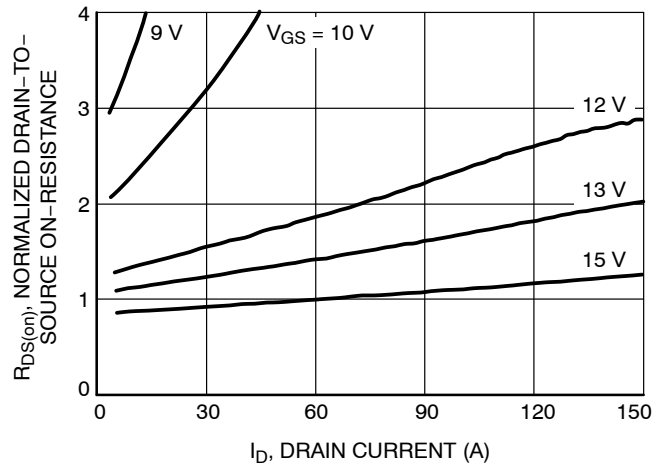


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

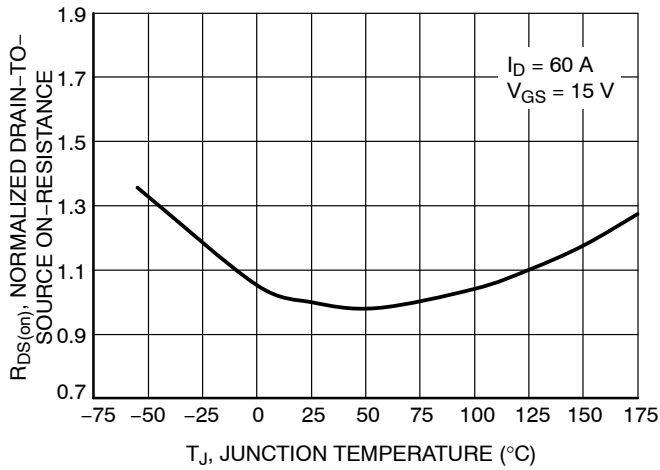


Figure 3. On-Resistance Variation with Temperature

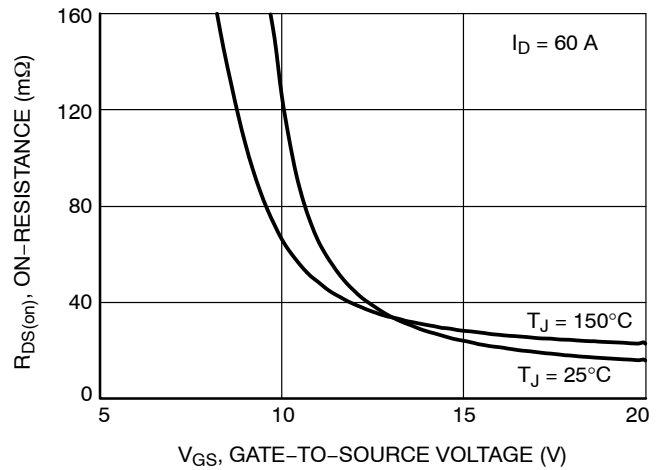


Figure 4. On-Resistance vs. Gate-to-Source Voltage

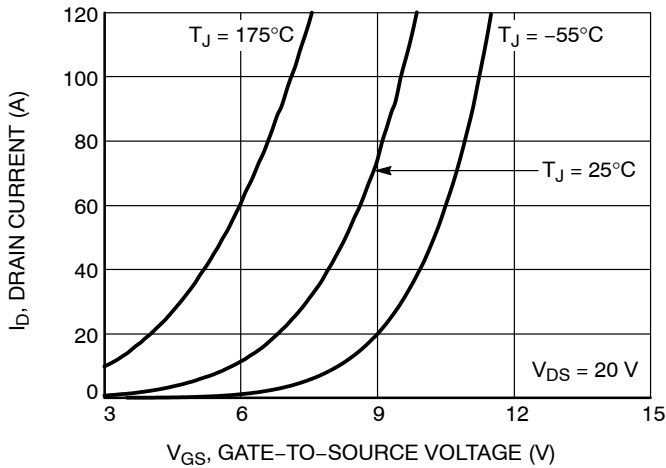


Figure 5. Transfer Characteristics

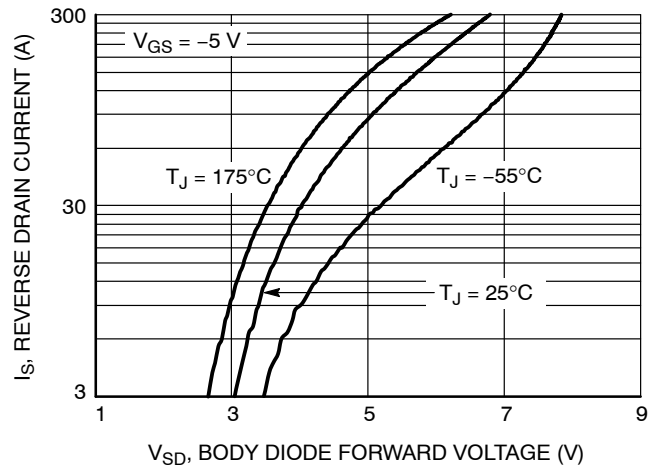


Figure 6. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

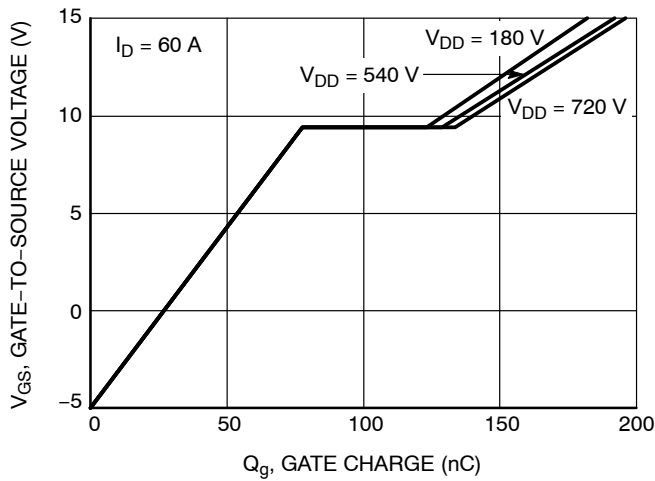


Figure 7. Gate-to-Source Voltage vs. Total Charge

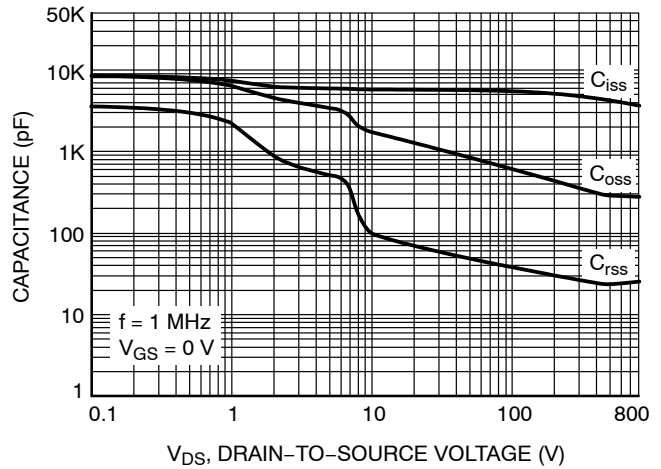


Figure 8. Capacitance vs. Drain-to-Source Voltage

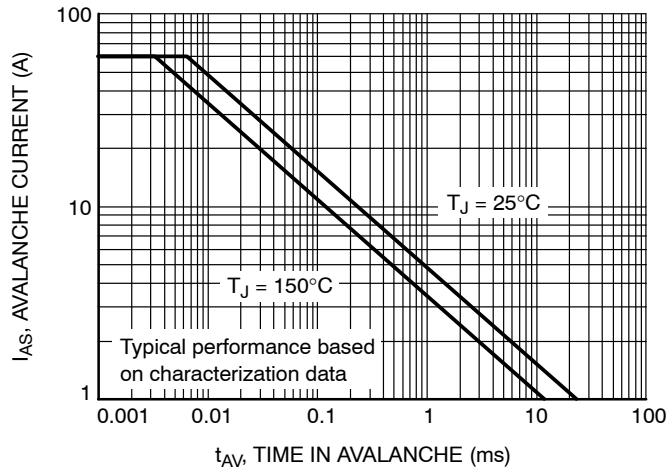


Figure 9. Unclamped Inductive Switching Capability

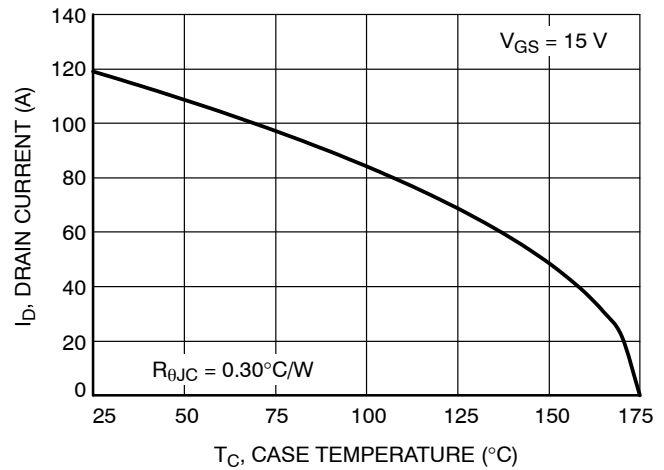


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

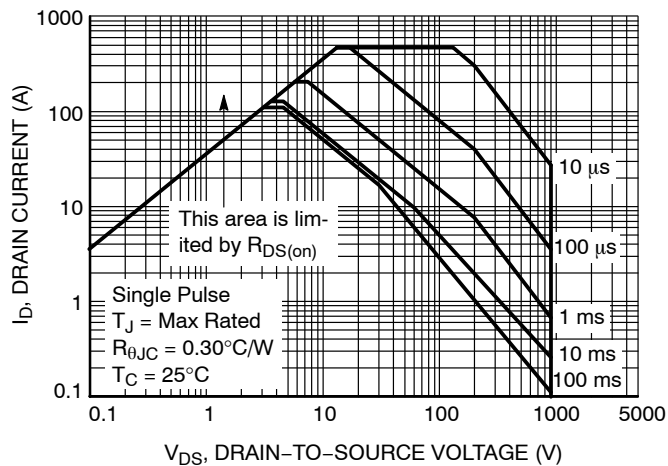


Figure 11. Safe Operating Area

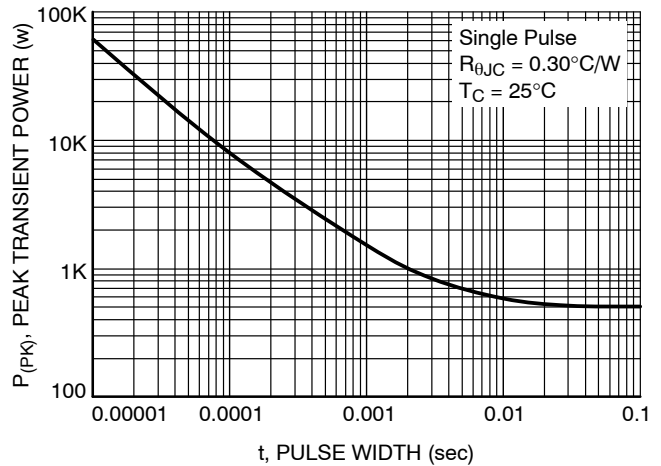


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS

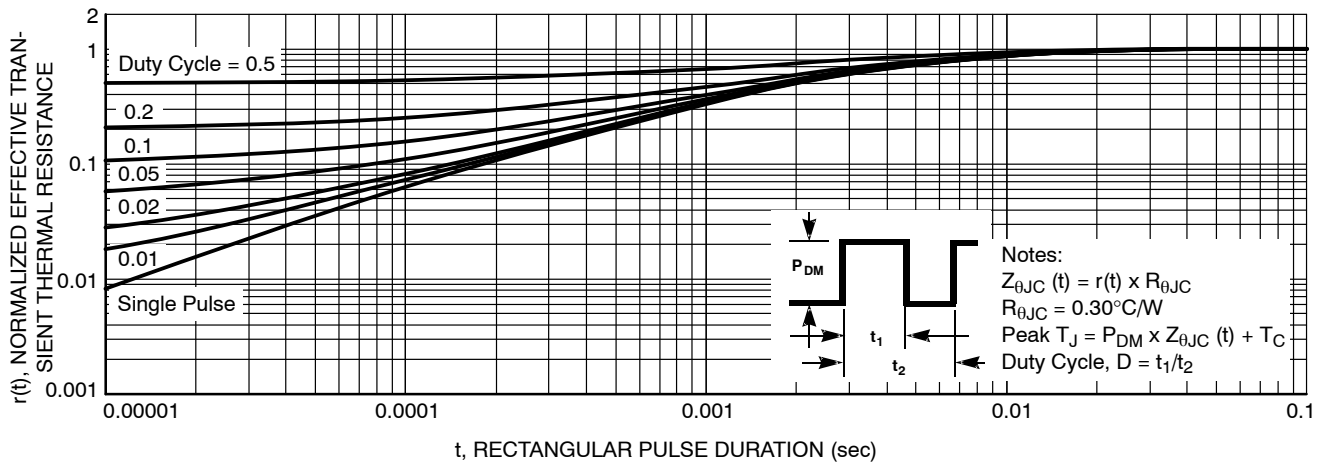


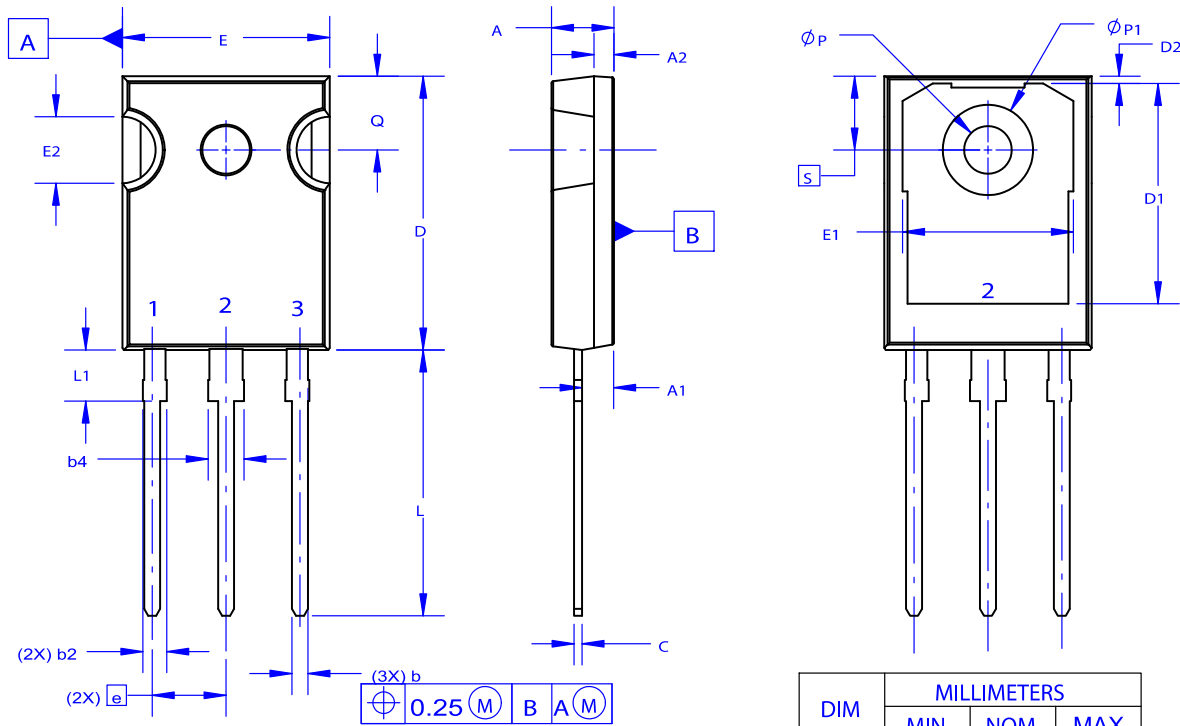
Figure 13. Junction-to-Ambient Transient Thermal Response Curve

PACKAGE MARKING AND ORDERING INFORMATION

| Part Number    | Top Marking    | Package             | Packing Method | Reel Size | Tape Size | Quantity |
|----------------|----------------|---------------------|----------------|-----------|-----------|----------|
| NVHL020N090SC1 | NVHL020N090SC1 | TO-247<br>Long Lead | Tube           | N/A       | N/A       | 30 Units |

PACKAGE DIMENSIONS

TO-247-3LD  
CASE 340CX  
ISSUE O



NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

B. ALL DIMENSIONS ARE IN MILLIMETERS.

C. DRAWING CONFORMS TO ASME Y14.5 - 2009.

D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

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